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MCP87030

High-Speed N-Channel Power MOSFET

Features:

- Low Drain-to-Source On Resistance (R_{DS(ON)})
- Low Total Gate Charge (Q_G) and Gate-to-Drain Charge (Q_GD)
- · Low Series Gate Resistance (R_G)
- · Fast Switching
- · Capable of Short Dead-Time Operation
- · RoHS Compliant

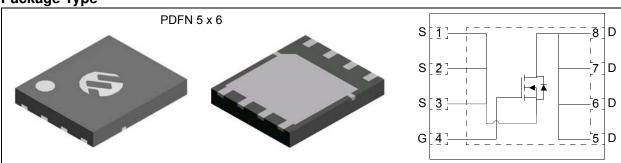
Applications:

- · Point-of-Load DC-DC Converters
- High-Efficiency Power Management in Servers, Networking and Automotive Applications

Description:

The MCP87030 is an N-Channel power MOSFET in a popular PDFN 5 mm x 6 mm package. Advanced packaging and silicon processing technologies allow the MCP87030 to achieve a low $Q_{\rm G}$ for a given $R_{\rm DS(on)}$ value, resulting in a low Figure of Merit (FOM). Combined with low $R_{\rm G}$, the low FOM of the MCP87030 allows high efficiency power conversion with reduced switching and conduction losses.

Package Type



Product Summary Table: Unless otherwise indicated, T _A = +25°C									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Operating Characteristics									
Drain-to-Source Breakdown Voltage	BV _{DSS}	25	_	_	V	$V_{GS} = 0V$, $I_D = 250 \mu A$			
Gate-to-Source Threshold Voltage	V _{GS(TH)}	1	1.3	1.6	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			
Drain-to-Source On Resistance	R _{DS(ON)}	_	3.3	4	mΩ	V _{GS} = 4.5V, I _D = 20A			
		_	2.8	3.5	mΩ	V _{GS} = 10V, I _D = 20A			
Total Gate Charge	Q_G	_	17	22	nC	V_{DS} = 12.5V, I_{D} = 20A, V_{GS} = 4.5V			
Gate-to-Drain Charge	Q_{GD}	_	6.7	_	nC	V _{DS} = 12.5V, I _D = 20A			
Series Gate Resistance	R_{G}	_	1.2	_	Ω	_			
Thermal Characteristics									
Thermal Resistance Junction-to-X	$R_{\theta JX}$	_	_	55	°C/W	Note 1			
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	_	_	1.2	°C/W	Note 2			

- **Note 1:** R_{0,JX} is determined with the device surface mounted on a 4-Layer FR4 PCB, with a 1" x 1" mounting pad of 2 oz. copper. This characteristic is dependent on user's board design.
 - 2: $R_{\theta JC}$ is determined using JEDEC 51-14 Method. This characteristic is determined by design.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

V _{DS}	+25V
V _{GS}	+10.0V / -8V
I _{D,} Continuous	100A, T _C = +25°C
P _D	2.2W, T _A = +25°C
T _J , T _{STG}	55°C to +150°C
E _{AS} Avalanche Energy	450 mJ
$I_D = 30A, L = 1 \text{ mH}, R_G =$: 25Ω

† Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Electrical Characteristics: Unless otherwise indicated, T _A = +25°C									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Static Characteristics									
Drain-to-Source Breakdown Voltage	BV _{DSS}	25	_	_	V	$V_{GS} = 0V, I_{D} = 250 \mu A$			
Drain-to-Source Leakage Current	I _{DSS}	_	_	1	μA	V _{GS} = 0V, V _{DS} = 20V			
Gate-to-Source Leakage Current	I _{GSS}	_	_	100	nA	$V_{DS} = 0V, V_{GS} = 10V/-8V$			
Gate-to-Source Threshold Voltage	V _{GS(TH)}	1	1.3	1.6	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$			
Drain-to-Source On Resistance	R _{DS(ON)}	_	4	_	mΩ	$V_{GS} = 3.3V, I_D = 20A$			
		_	3.3	4	mΩ	$V_{GS} = 4.5V, I_D = 20A$			
		_	2.8	3.5	mΩ	V _{GS} = 10V, I _D = 20A			
Transconductance	9 _{fs}	_	113	_	S	V _{DS} = 12.5V, I _D = 20A			
Dynamic Characteristics									
Input Capacitance	C _{ISS}	_	1635	_	pF	V _{GS} = 0V, V _{DS} = 12.5V, f = 1 MHz			
Output Capacitance	C _{OSS}	_	730	_	pF	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1 MHz$			
Reverse Transfer Capacitance	C _{RSS}	_	160	_	pF	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1 MHz$			
Total Gate Charge	Q_{G}	_	17	22	nC	V_{DS} = 12.5V, I_{D} = 20A, V_{GS} = 4.5V			
Gate-to-Drain Charge	Q_{GD}	_	6.7	_	nC	V _{DS} = 12.5V, I _D = 20A			
Gate-to-Source Charge	Q_{GS}	_	3.2	_	nC	V _{DS} = 12.5V, I _D = 20A			
Gate Charge at V _{GS(TH)}	Q _{G(TH)}	_	2.1	_	nC	V _{DS} = 12.5V, I _D = 20A			
Output Charge	Q _{OSS}	_	14.3	_	nC	V _{DS} = 12.5V, V _{GS} = 0			
Turn-On Delay Time	t _{d(on)}		5	_	ns	V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 20A, R_{G} = 2 Ω			
Rise Time	t _r	_	17	_	ns	V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 20A, R_{G} = 2 Ω			
Turn-Off Delay Time	t _{d(off)}	_	14	_	ns	V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 20A, R_{G} = 2 Ω			
Fall Time	t _f	_	16	_	ns	V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 20A, R_{G} = 2 Ω			
Series Gate Resistance	R_{G}	_	1.2	_	Ω				

DC ELECTRICAL CHARACTERISTICS (CONTINUED)

Electrical Characteristics: Unless otherwise indicated, T _A = +25°C									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Diode Characteristics									
Diode Forward Voltage	V _{FD}	_	0.8	1	V	I _S = 20A, V _{GS} = 0V			
Reverse Recovery Charge	Q _{RR}	_	32	_	nC	I _S = 20A, di/dt = 300 A/μs			
Reverse Recovery Time	t _{rr}	_	20	_	ns	I _S = 20A, di/dt = 300 A/μs			
Avalanche Characteristics									
Avalanche Energy	E _{AS}	112.5	_	_	mJ	I_D = 15A, L = 1 mH, R _G = 25 Ω			

TEMPERATURE CHARACTERISTICS

Electrical Characteristics: Unless otherwise indicated, T _A = +25°C							
Parameters Sym. Min. Typ. Max. Units Conditions							
Temperature Ranges							
Operating Junction Temperature Range	TJ	-55	_	150	°C		
Storage Temperature Range	T _A	-55	_	150	°C		
Package Thermal Resistances							
Thermal Resistance Junction-to-X, 8L 5x6-PDFN	$R_{\theta JX}$	_	_	55	°C/W	Note 1	
Thermal Resistance Junction-to-Case, 8L 5x6-PDFN	$R_{\theta JC}$	_	_	1.2	°C/W	Note 2	

Note 1: R_{0JX} is determined with the device surface mounted on a 4-Layer FR4 PCB, with a 1" x 1" mounting pad of 2 oz. copper. This characteristic is dependent on user's board design.

^{2:} $R_{\theta JC}$ is determined using JEDEC 51-14 Method. This characteristic is determined by design.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25$ °C.

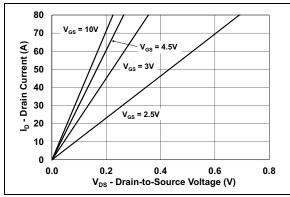


FIGURE 2-1: Typical Output Characteristics.

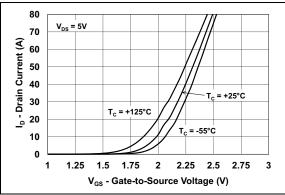


FIGURE 2-2: Typical Transfer Characteristics.

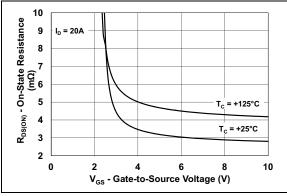


FIGURE 2-3: On Resistance vs. Gate-to-Source Voltage.

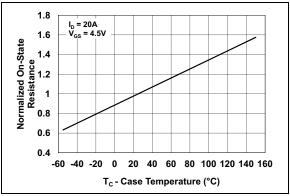


FIGURE 2-4: Normalized On Resistance vs. Temperature.

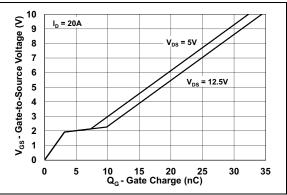


FIGURE 2-5: Gate-to-Source Voltage vs. Gate Charge.

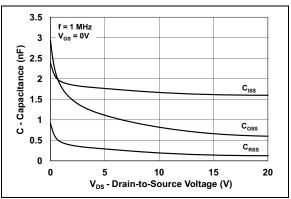


FIGURE 2-6: Capacitance vs. Drain-to-Source Voltage.

Note: Unless otherwise indicated, $T_A = +25$ °C.

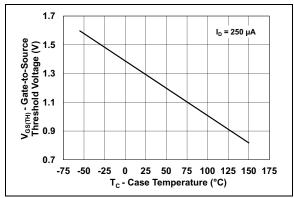


FIGURE 2-7: Gate-to-Source Threshold Voltage vs. Temperature.

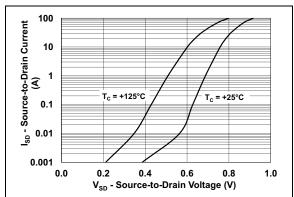


FIGURE 2-8: Source-to-Drain Current vs. Source-to-Drain Voltage.

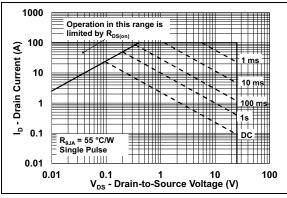


FIGURE 2-9: Maximum Safe Operating Area.

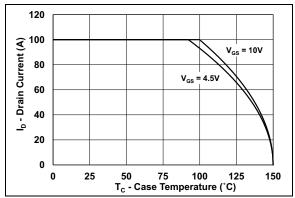


FIGURE 2-10: Maximum Drain Current vs. Temperature.

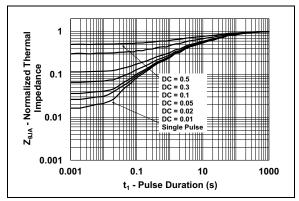


FIGURE 2-11: Transient Thermal Impedance.

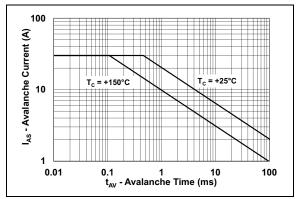


FIGURE 2-12: Single-Pulse Unclamped Inductive Switching.

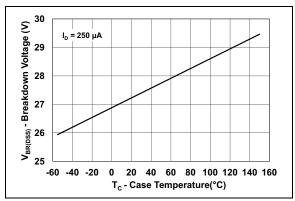


FIGURE 2-13: Drain-to-Source Breakdown Voltage vs. Temperature.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

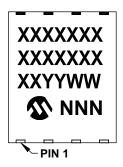
TABLE 3-1: PIN FUNCTION TABLE

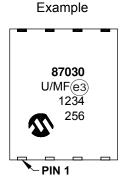
MCP87030 5x6 PDFN	Symbol	Description
1, 2, 3	S	Source pin
4	G	Gate pin
5, 6, 7, 8	D	Drain pin, including exposed thermal pad

4.0 PACKAGING INFORMATION

4.1 Package Marking Information*

8-Lead PDFN (5x6x1.0 mm)





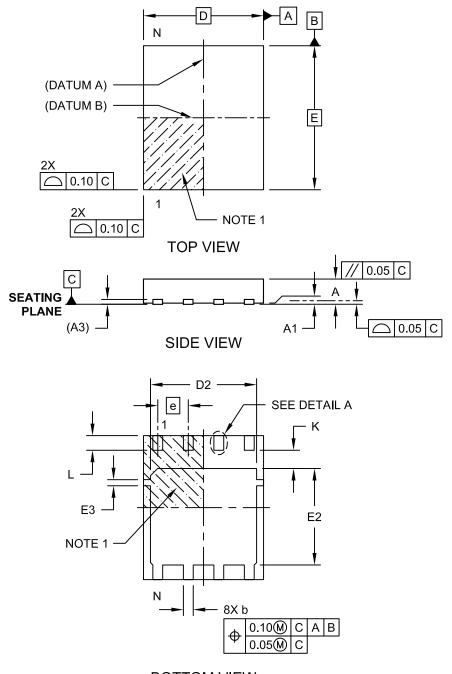
*RoHS compliant using EU-RoHS exemption: 7(a) – Lead in high-melting-temperature-type solders (i.e., lead-based alloys containing 85% by weight or more lead) can be found on the outer packaging for this package.

Legend: XX...X Customer-specific information
Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code
Pb-free JEDEC designator for Matte Tin (Sn)
This package is Pb-free. The Pb-free JEDEC designator (e3)
can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

8-Lead Power Dual Flatpack No Lead Package (MF) - 5x6x1.0 mm Body [PDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



BOTTOM VIEW

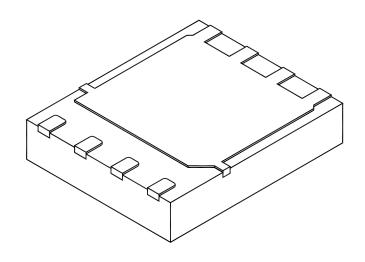
Microchip Technology Drawing C04-188B Sheet 1 of 2

Note:

8-Lead Power Dual Flatpack No Lead Package (MF) - 5x6x1.0 mm Body [PDFN]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





	Units	MILLIMETERS				
Dimension	Limits	MIN	NOM	MAX		
Number of Pins	N		8			
Pitch	е		1.27 BSC			
Overall Height	Α	0.80	1.00	1.03		
Standoff	A1	0.00	-	0.05		
Terminal Thickness	(A3)	0.20 REF				
Overall Length	D	5.00 BSC				
Overall Width	E	6.00 BSC				
Exposed Pad length	D2	4.27	4.42	4.52		
Exposed Pad Width	E2	3.87	4.02	4.12		
Tab Width	E3	0.20	0.25	0.30		
Terminal Width	b	0.36	0.41	0.46		
Terminal Length	L	0.51	0.61	0.71		
Terminal to Exposed Pad	K	0.71	0.76	0.81		

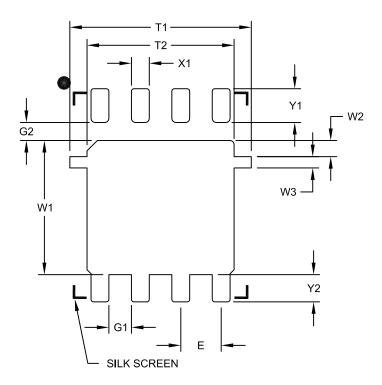
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package is saw singulated.
- 3. Package dimension does not include mold flash, protrusions, burrs or metal smearing.
- 4. Dimensioning and tolerancing per ASME Y14.5M.
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 - REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-188B Sheet 2 of 2

8-Lead Power Dual Flatpack No Lead Package (MF) – 5x6x1.0 mm Body [PDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units			S
Dimension	Dimension Limits			MAX
Contact Pitch	Е			
Center Pad Width	W1			4.22
Pad Edge to Tab	W2		0.51	
Tab Width	W3		0.35	
Center Pad Length With Tabs	T1			5.70
Center Pad Length	T2			4.62
Distance Between Terminals	G1	0.71		
Terminal To Center Pad (X4)	G2	0.57		
Terminal Pad Width (X8)	X1			0.56
Terminal Pad Length (X4)	Y1			1.06
Terminal Pad Length (X8)	Y2			0.86

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2188A

APPENDIX A: REVISION HISTORY

Revision B (July 2013)

The following is the list of modifications.

- 1. Updated the Thermal Resistances maximum values in the Temperature Characteristics table.
- 2. Added Figure 2-9, Figure 2-10 and Figure 2-11.

Revision A (January 2013)

· Original Release of this Document.

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

	X X X Y Y Y Y Y Y Y Y Y Y Y Y Y Y Y Y Y	•	Ex a)	xamples: MCP87030T-U/MF:	Tape and Reel, Ultra-High Temperature, 8LD PDFN package
Device:	MCP87030T: N-Chann	el Power MOSFET (Tape and	Reel)		
Temperature Range	e: U = -55°C to +150°C (Jltra High)			
Package:	MF = 8-Lead High Powe (5x6x1.0 mm Body	r Dual Flatpack, No Lead Pac) (PDFN), 8-lead	ckage		

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